

# 1.52mm×1.52mm Silicon PD Chip datasheet

P/N: WS9L-10B

## Application

Si NIP photodiode chips

## Structure

Planar type : NIP diode

Electrodes :

Top side ( Cathode ) : Al

Backside ( Anode ) : Au Alloy

## DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	53 × 53			mil
Chip width	60 × 60 ( ± 1.0 )			mil
Chip length	60 × 60 ( ± 1.0 )			mil
Chip height	12 ( ± 1.0 )			mil
Pad N( Cathode )	15.6 × 9.2			mil
Pad P(Anode )	15.6 × 9.2			mil

## Electro-Optical Characteristics ( @ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.7		1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR=3V, F=1 MHz		25		pF

Unit : mil

